Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A thin film forming method which ~~generates~~ makes a ~~particulate thin film~~ material, which becomes a source of thin films to be formed, particulate, introduces and deposits the particulate ~~thin film~~ material~~, which is generated,~~ on a first principal surface ~~of a substrate~~and a second principal surface, opposite to said first principal surface, of a substrate, and forms ~~a thin film~~thin films simultaneously on the first principal surface and the second principal surface of the substrate, comprising ~~characterized by supporting the substrate so that a first principal surface and its backside (hereafter, this is called a second principal surface) may be exposed~~ exposing the first principal surface and the second principal surface of the substrate, and introducing the particulate material, including converging the particulate material and increasing its density in the introducing of the particulate material~~, generating the particulate thin film material on an extension of an in-plane direction of the first principal surface of the substrate, and introducing the particulate thin film material, which is generated,~~ on the first principal surface and the second principal surface of the substrate.

2. (Canceled)

3. (Currently Amended) The thin film forming method according to claim 1, ~~characterized by~~further including depositing the ~~thin film~~ particulate material while ~~with~~ rotating the substrate about a rotational axis that is ~~with making a~~ normal ~~direction of~~ to the first principal surface ~~as a rotation axis~~.

4. (Currently Amended) The thin film forming method according to claim 1, further including~~characterized by~~ arranging heaters in a position facing the first principal surface and a position facing the second principal surface ~~on the first principal surface and the second principal surface~~ of the substrate and heating the substrate.

5.(Previously Presented) The thin film forming method according to claim 1, further including~~characterized by~~ generating the particulate ~~thin film~~ material from a material used for formation of an oxide superconductor.

6. (Currently Amended) A thin film forming apparatus which is equipped with a target ~~constructed~~ made of a ~~thin film~~ material which becomes a source of a thin film to be formed, a cathode for generating ~~a particulate thin film~~ the material, which is particulate, from the target, a supporting member for supporting ~~the substrate~~ a substrate on which the ~~particulate thin film~~ particulate material is ~~to be~~ deposited, a heater for heating the substrate, and a guide for introducing the particulate ~~thin film~~ material onto a first principal surface of the substrate and a second principal surface of the substrate, opposite to said first principal surface, ~~where the thin film material is deposited, characterized in that the~~ further comprising said supporting member supporting ~~supports~~ the substrate so as to expose the first principal surface and ~~its backside (~~the second principal surface~~)~~ of the substrate, ~~the target is disposed in a position for producing the particulate thin film material in an extension of an in-plane direction of the first principal surface of the substrate,~~ and the guide ~~is~~ being disposed ~~on~~ in a position facing the first principal surface of the substrate and in a position facing the second principal surface of the substrate.

7.(Currently Amended) The thin film forming apparatus according to claim 6, wherein ~~characterized in that~~ the guide has an inclined portion spaced apart form the substrate by a distance that becomes shorter along a direction of the introducing of the particulate material ~~is constructed of a parallel portion parallel to the first principal surface or the second principal surface of the substrate, and an inclined portion which is separate from the substrate as is goes to the target from the substrate~~.

8.(Currently Amended) The thin film forming apparatus according to ~~claim 5~~claim 6, wherein~~characterized in that~~ the supporting member comprises a rotating mechanism which rotates the substrate in a direction normal to the first principal surface of the substrate as an axis of rotation.

9.(Previously Presented) The thin film forming apparatus according to claim 6, wherein~~characterized in that~~ the heater is provided on a surface of each guide which faces the substrate.

10.(Currently Amended) The thin film forming apparatus according to claim 6, wherein ~~characterized in that~~ the target is arranged so that the particulate ~~thin film~~ material ~~generated~~ may be incident ~~into~~ onto the first principal surface ~~and the~~ or the second principal surface of the substrate at ~~an~~ a predetermined angle ~~determined beforehand~~.

11.(Previously Presented) The thin film forming apparatus according to claim 6, further including ~~characterized by comprising the~~ two or more of the targets.

12.(Currently Amended) The thin film forming apparatus according to claim 6, wherein ~~characterized in that~~ the target is ~~constructed~~ made of a material used for formation of an oxide superconductor.